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Application No. <u>10/786,726</u>	Prepared by <u>DLA</u>	Tracking Number <u>05995918</u>	
Examiner-GAU <u>Hoang - 2818</u>	Date <u>9/17/04</u>	Week Date <u>8/16/04</u>	
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a. Serial No.	f. Foreign Priority	k. Print Claim(s)	<u>p. PTO-1449</u>
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

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**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
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Complete if Known

Application Number	10/786726
Filing Date	February 25, 2004
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

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Attorney Docket No: 303.680US3

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